

Darlington Transistors

NPN Silicon

MPSA28

MPSA29*

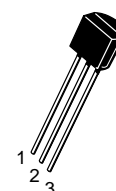
*ON Semiconductor Preferred Device

MAXIMUM RATINGS

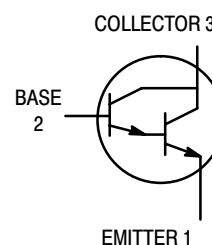
Rating	Symbol	MPSA28	MPSA29	Unit
Collector–Emitter Voltage	V_{CES}	80	100	Vdc
Collector–Base Voltage	V_{CBO}	80	100	Vdc
Emitter–Base Voltage	V_{EBO}	12		Vdc
Collector Current — Continuous	I_C	500		mA _{dc}
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625		mW
		5.0		mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5		Watts
		12		mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



CASE 29–11, STYLE 1
TO–92 (TO–226AA)



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 100\ \mu\text{A}_{dc}$, $V_{BE} = 0$)	MPSA28 MPSA29	$V_{(BR)CES}$	80 100	— —	— —	Vdc
Collector–Base Breakdown Voltage ($I_C = 100\ \mu\text{A}_{dc}$, $I_E = 0$)	MPSA28 MPSA29	$V_{(BR)CBO}$	80 100	— —	— —	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\ \mu\text{A}_{dc}$, $I_C = 0$)		$V_{(BR)EBO}$	12	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60\ \text{Vdc}$, $I_E = 0$) ($V_{CB} = 80\ \text{Vdc}$, $I_E = 0$)	MPSA28 MPSA29	I_{CBO}	— —	— —	100 100	nA _{dc}
Collector Cutoff Current ($V_{CE} = 60\ \text{Vdc}$, $V_{BE} = 0$) ($V_{CE} = 80\ \text{Vdc}$, $V_{BE} = 0$)	MPSA28 MPSA29	I_{CES}	— —	— —	500 500	nA _{dc}
Emitter Cutoff Current ($V_{EB} = 10\ \text{Vdc}$, $I_C = 0$)		I_{EBO}	—	—	100	nA _{dc}

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

MPSA28 MPSA29

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS⁽¹⁾

DC Current Gain ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 100\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	10,000 10,000	— —	— —	—
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.01\text{ mA}$) ($I_C = 100\text{ mA}$, $I_B = 0.1\text{ mA}$)	$V_{CE(sat)}$	— —	0.7 0.8	1.2 1.5	Vdc
Base–Emitter On Voltage ($I_C = 100\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$)	$V_{BE(on)}$	—	1.4	2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ⁽²⁾ ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	125	200	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	5.0	8.0	pF

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

2. $f_T = h_{fe} \cdot f_{test}$.

MPSA28 MPSA29

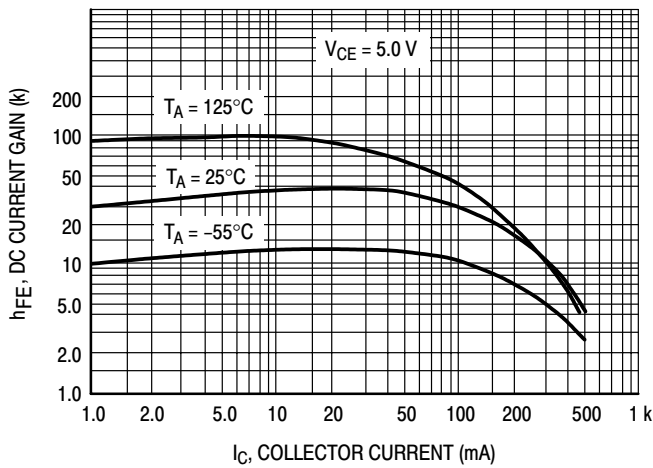


Figure 1. DC Current Gain

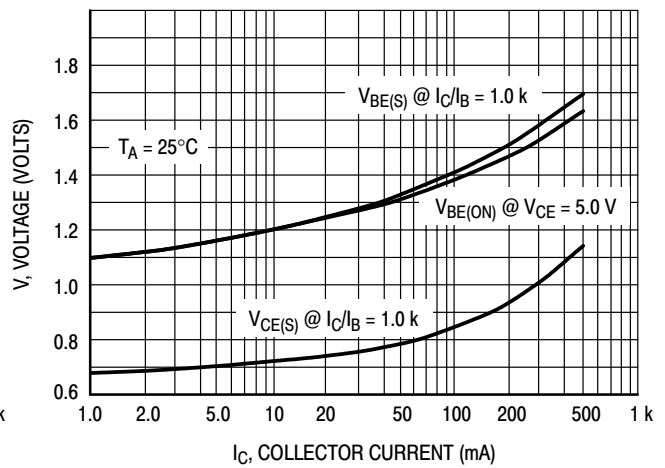


Figure 2. "ON" Voltages

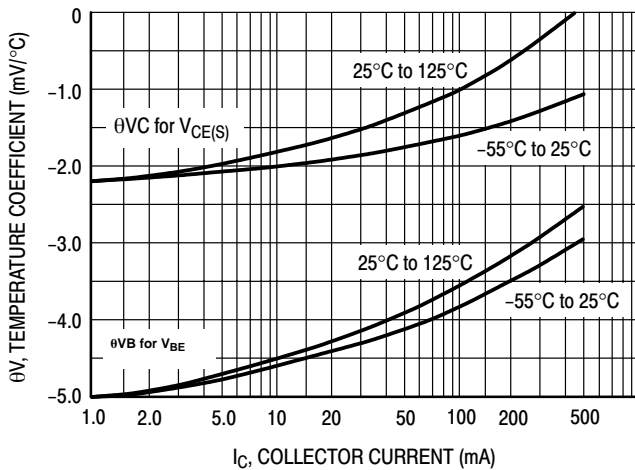


Figure 3. Temperature Coefficients

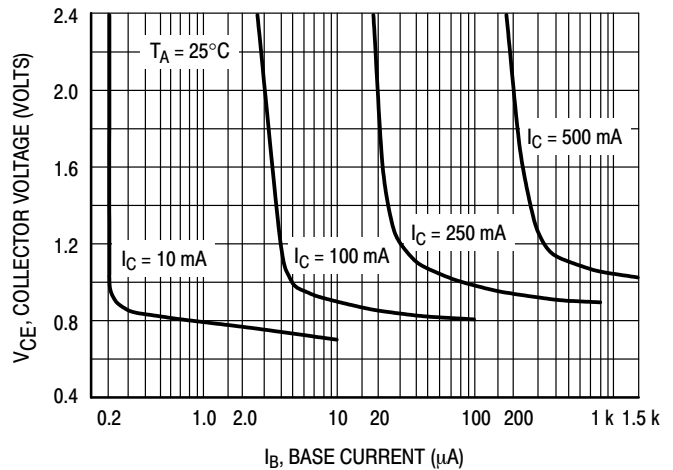


Figure 4. Collector Saturation Region

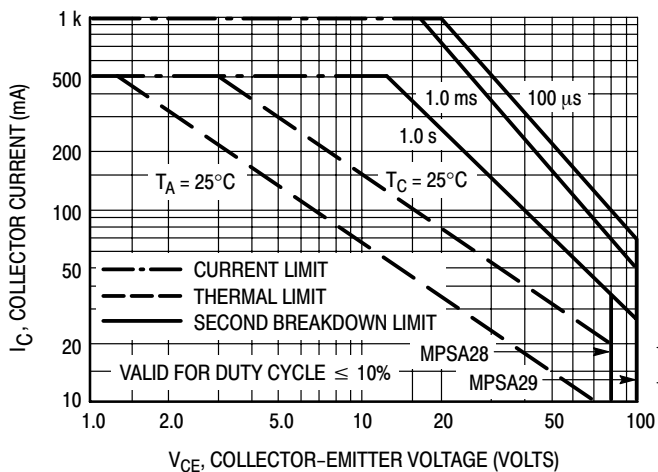


Figure 5. Active Region — Safe Operating Area

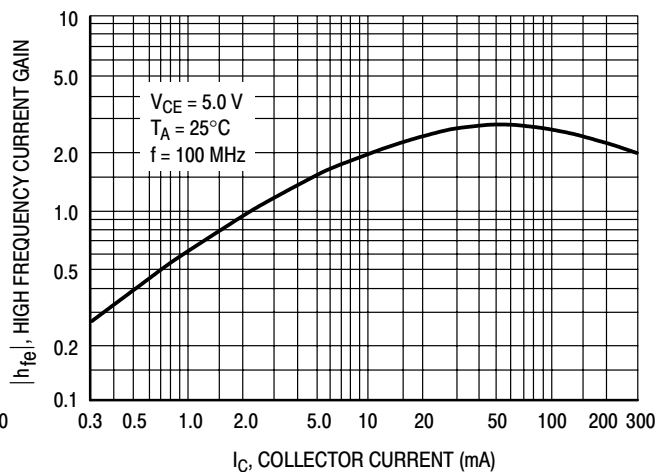
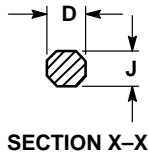
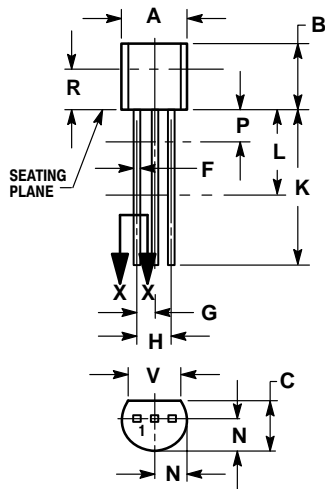


Figure 6. High Frequency Current Gain

MPSA28 MPSA29

PACKAGE DIMENSIONS



**CASE 029-11
(TO-226AA)
ISSUE AD**


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

1. PIN 1. EMITTER
2. BASE
3. COLLECTOR

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